

Figure 3

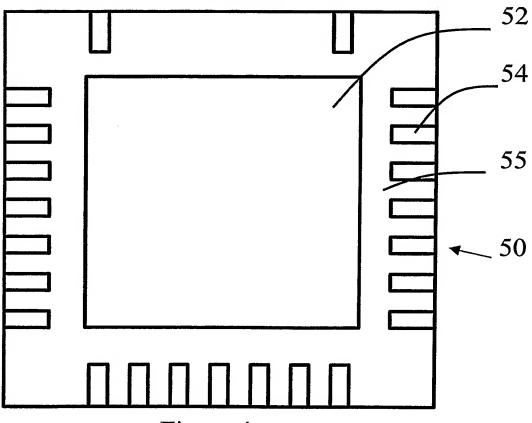


Figure 4

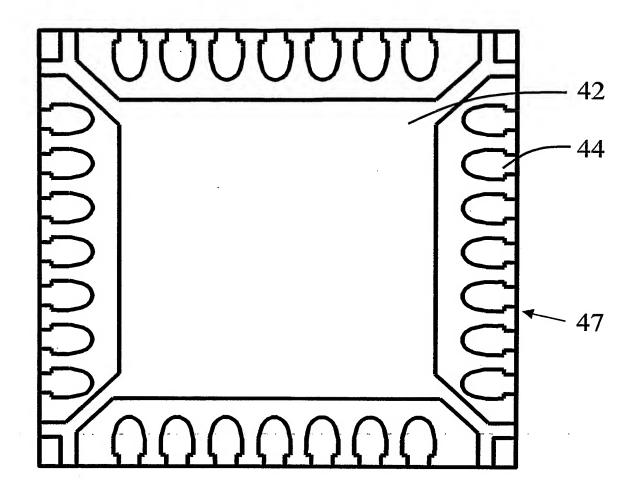
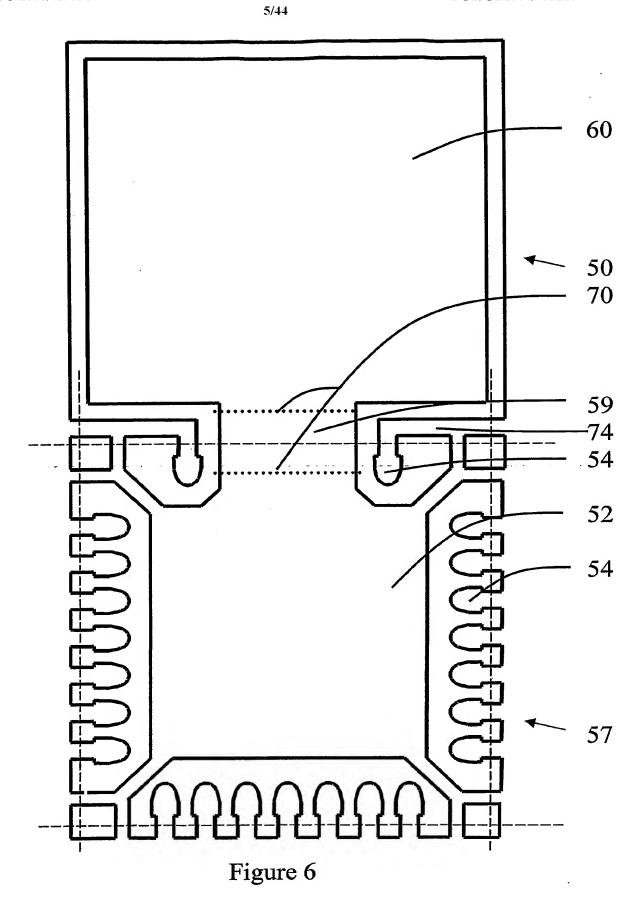


Figure 5



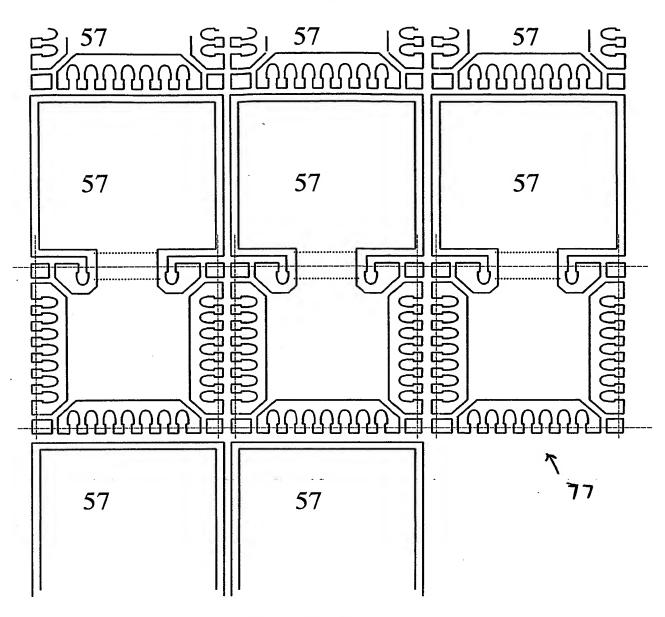


Figure 7

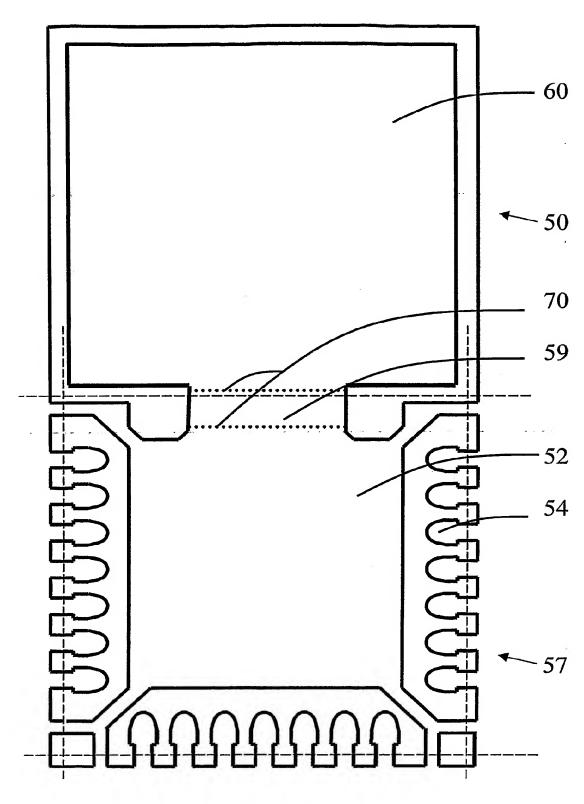
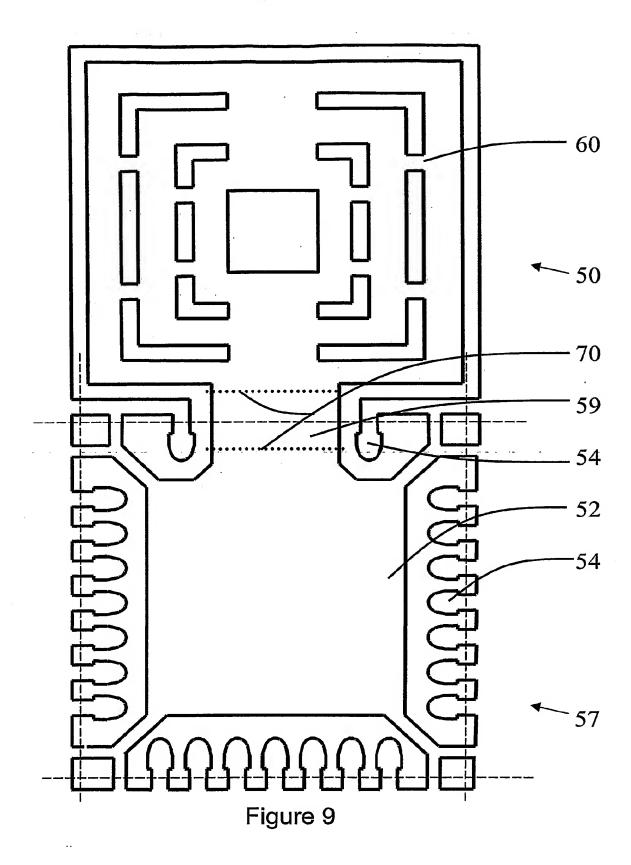
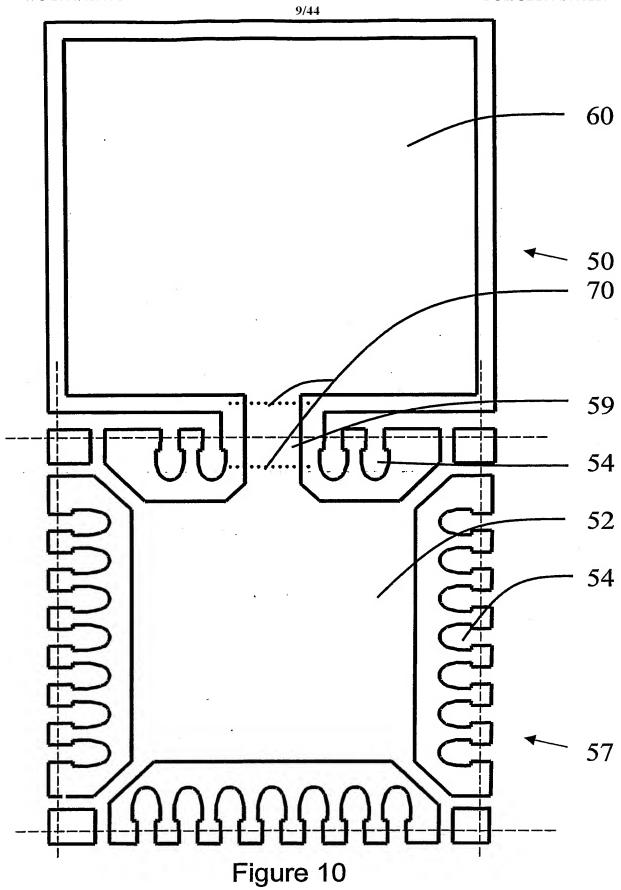


Figure 8





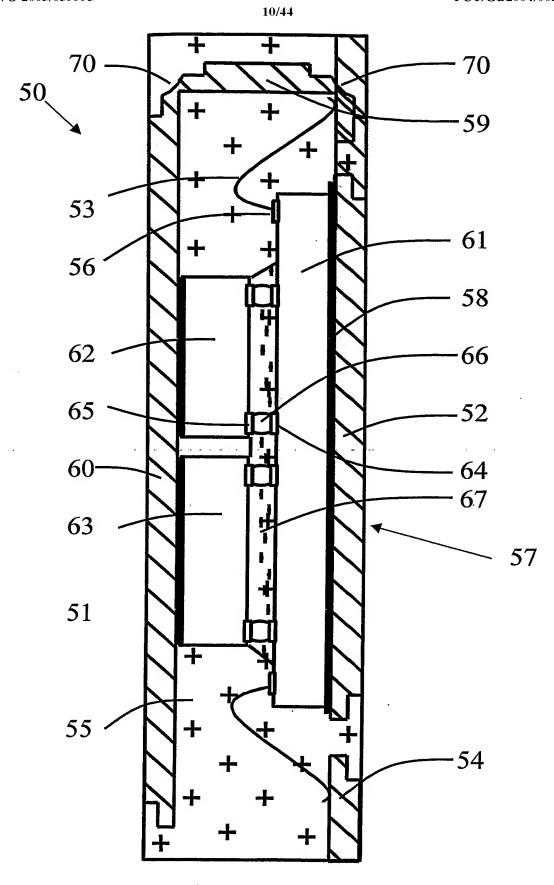


Figure 11

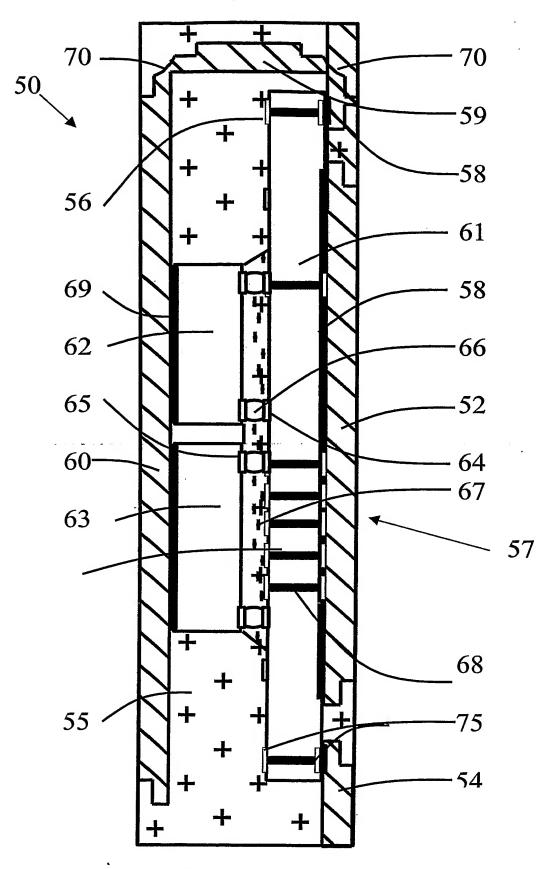


Figure 12



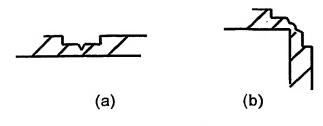


Figure 13

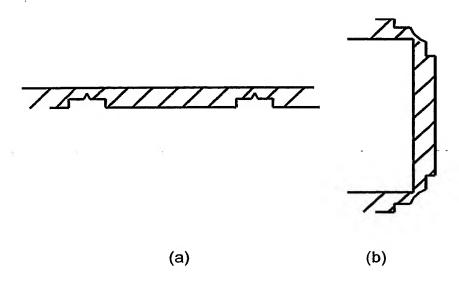


Figure 14

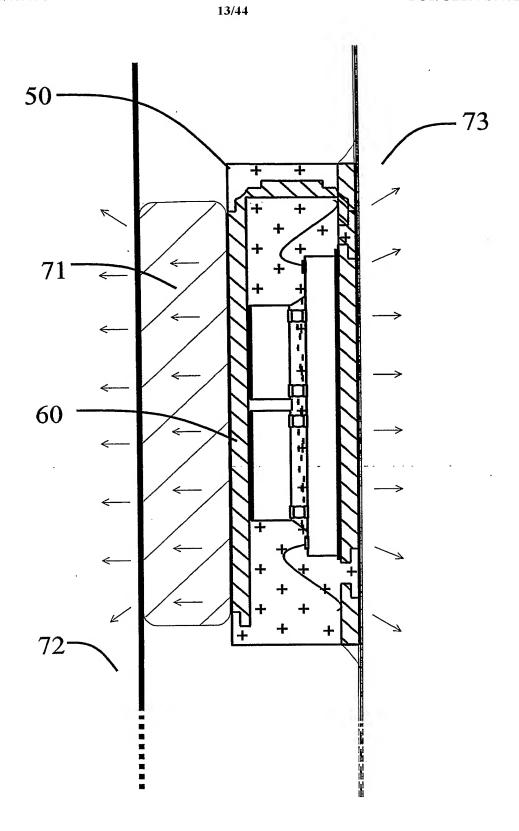


Figure 15

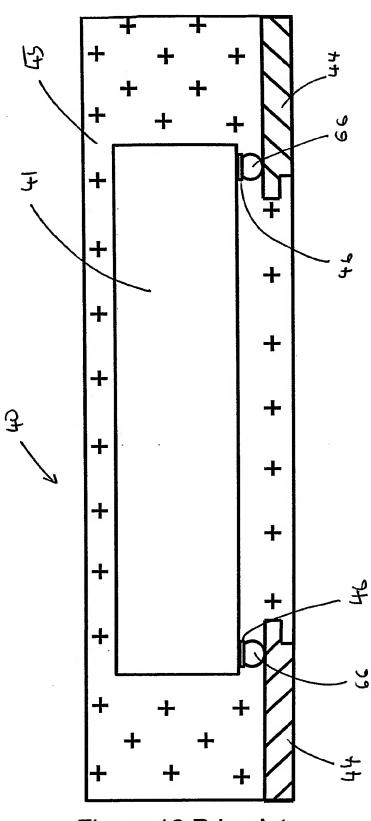


Figure 16 Prior Art

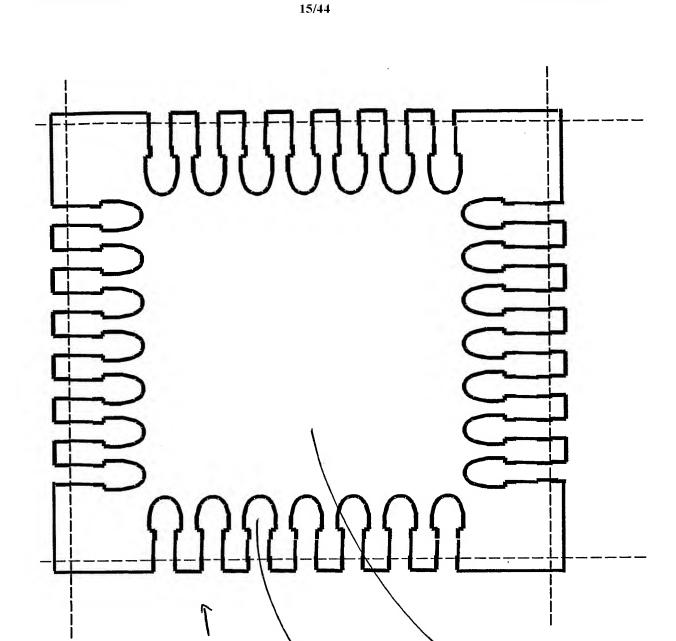
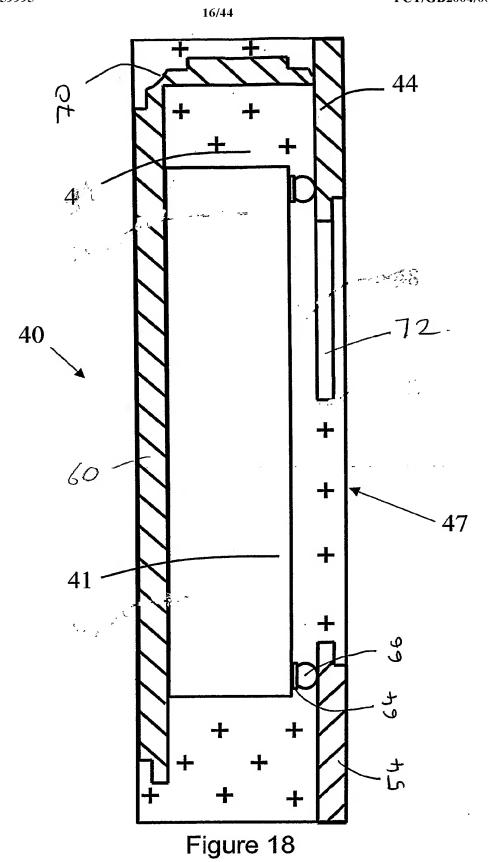


Figure 17 Prior Art





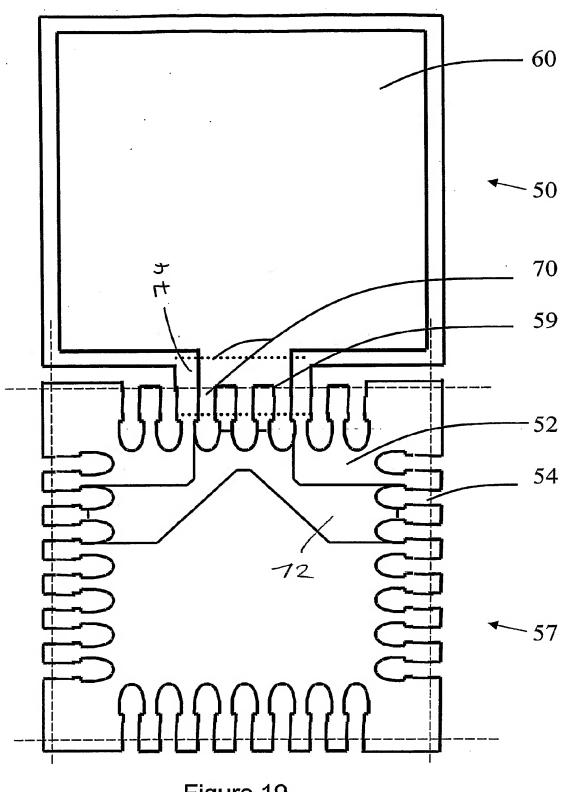
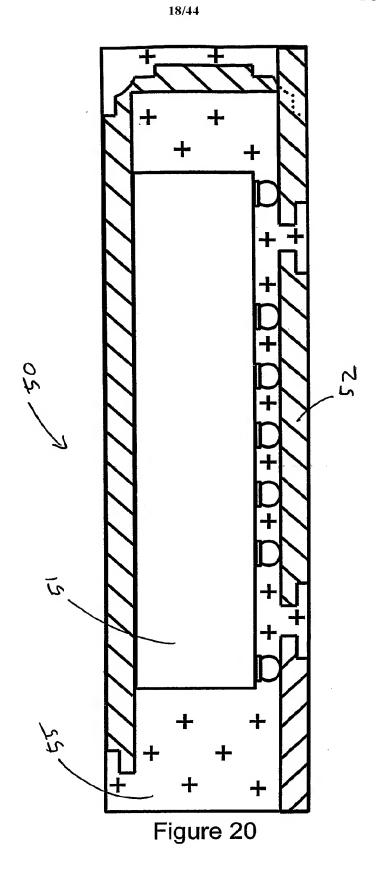
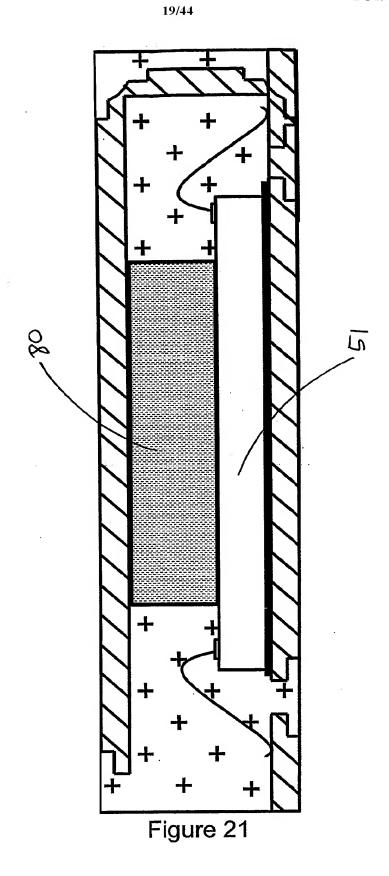
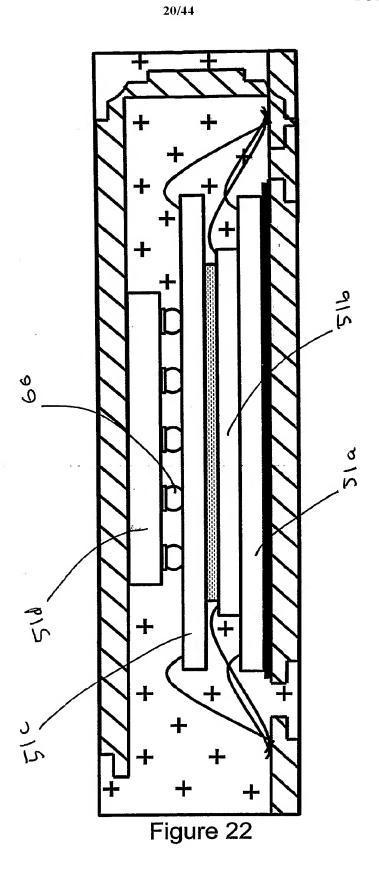
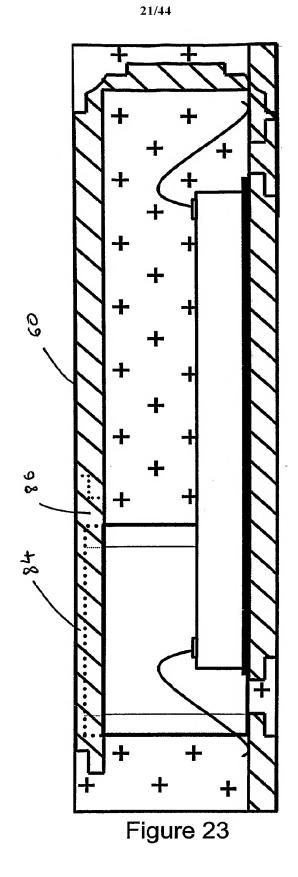


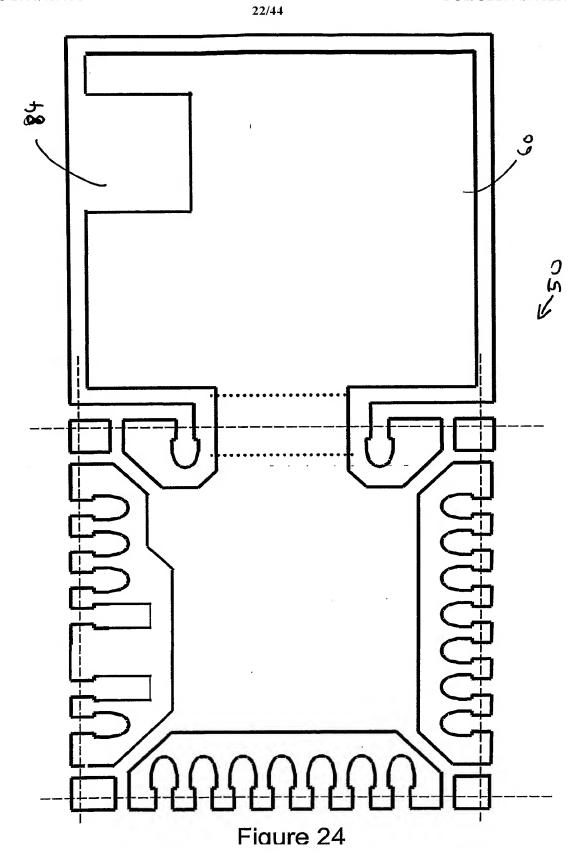
Figure 19

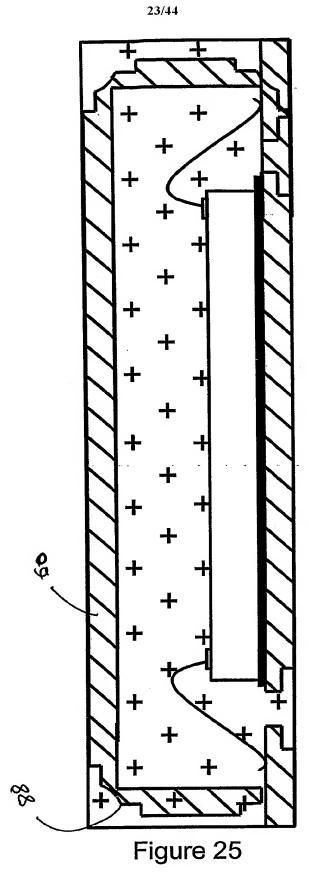


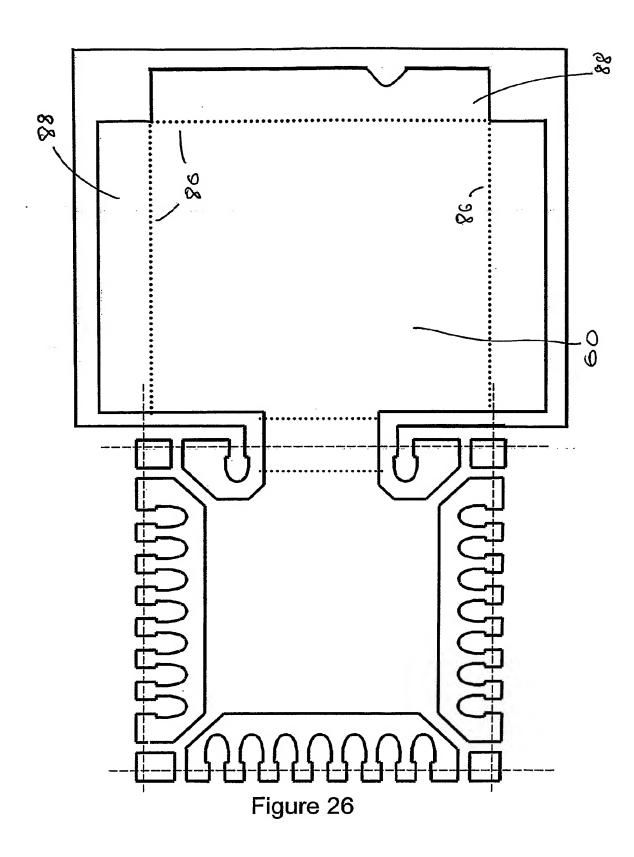


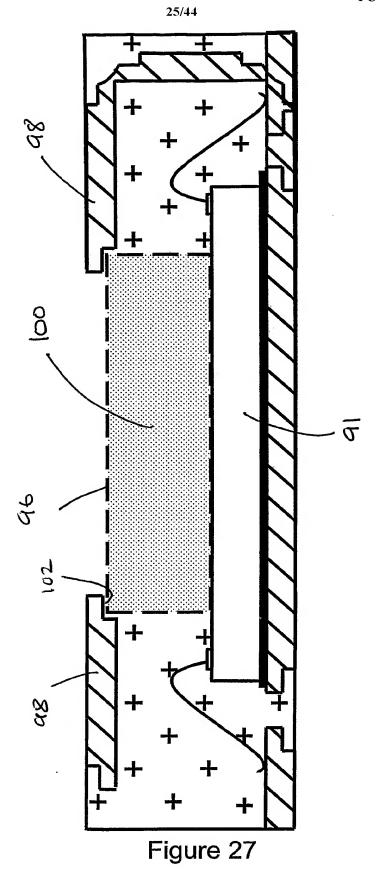


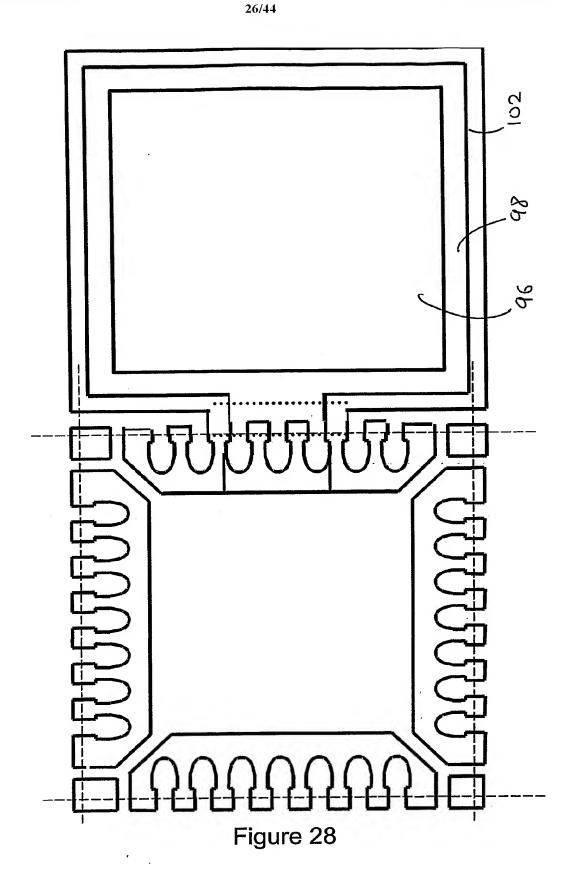


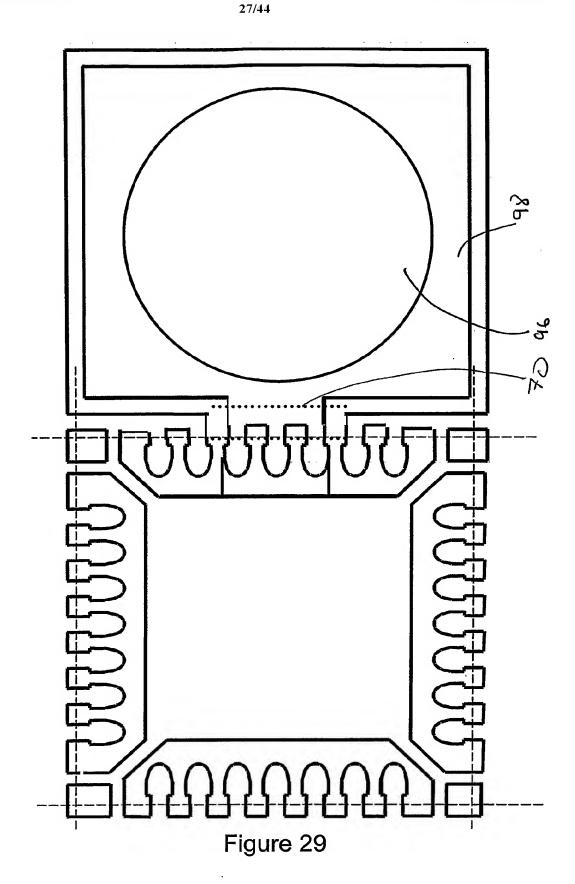


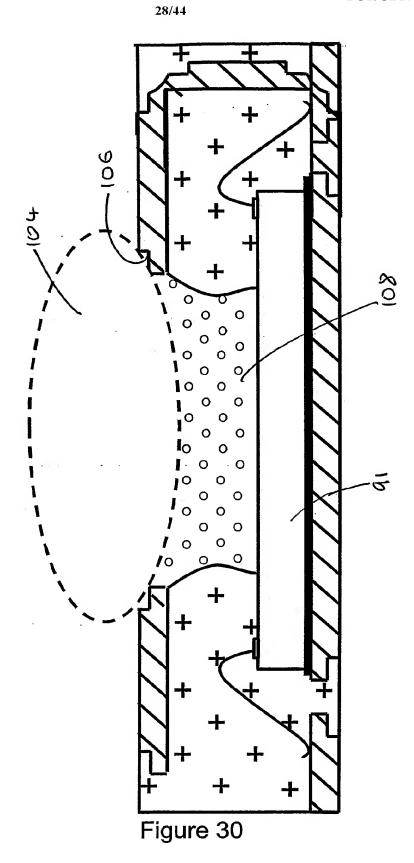




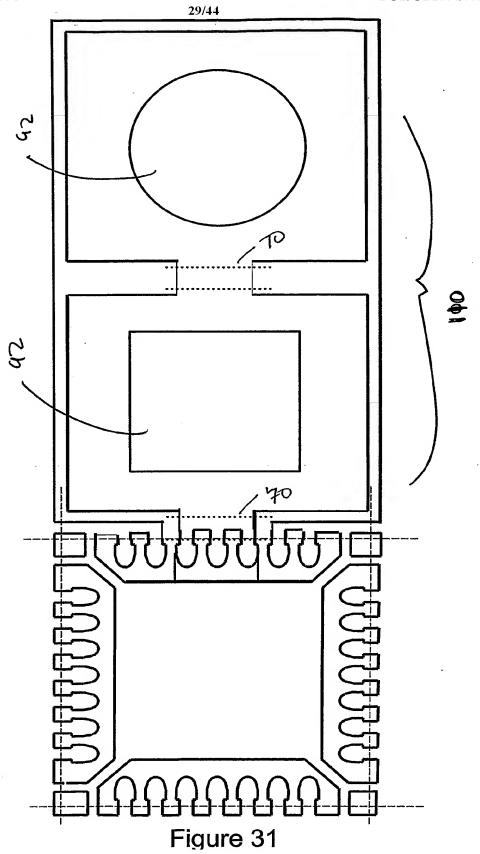








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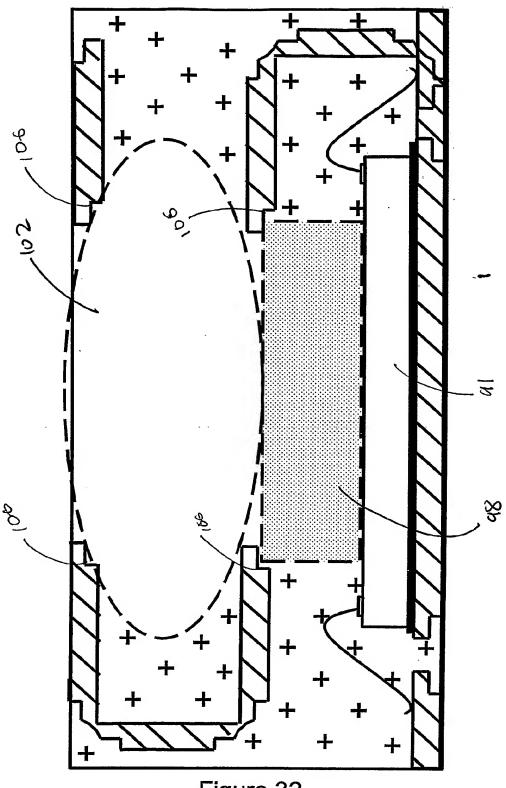


Figure 32

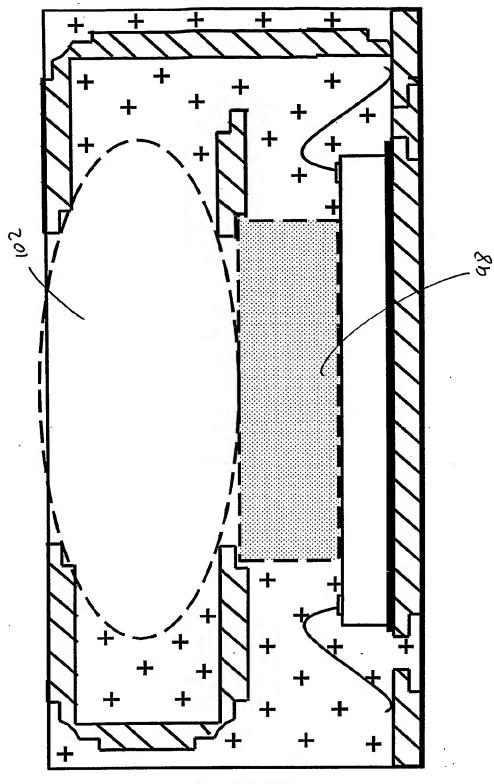
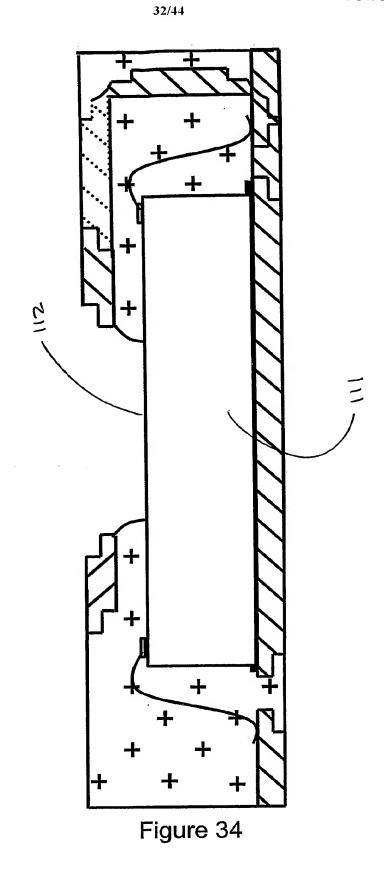
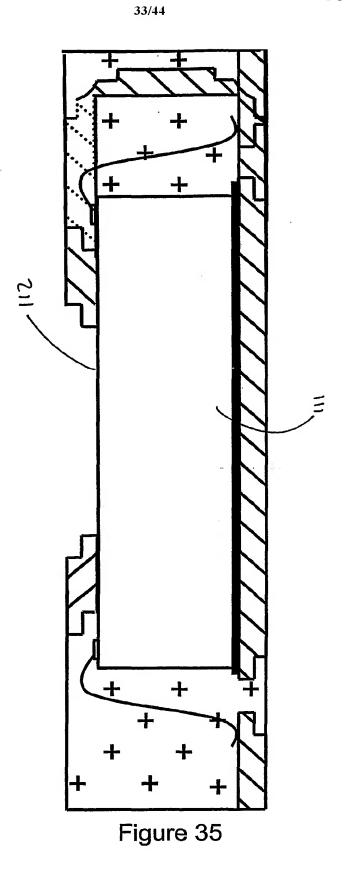
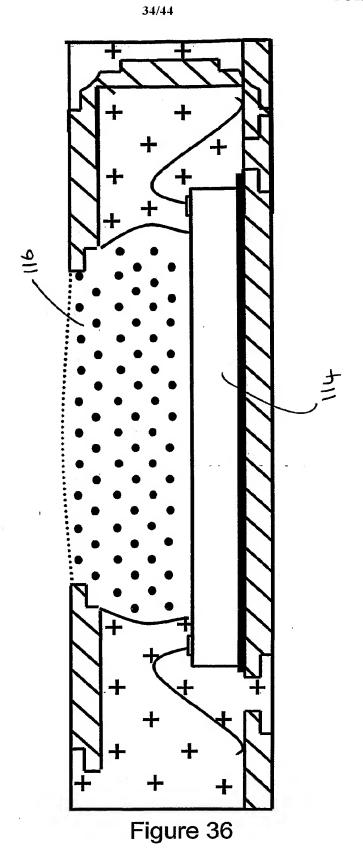
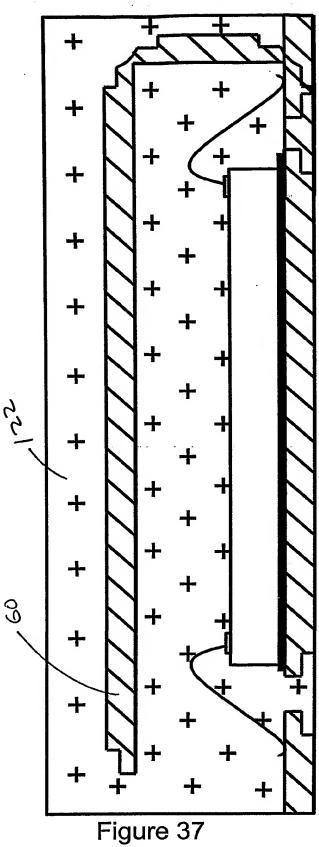


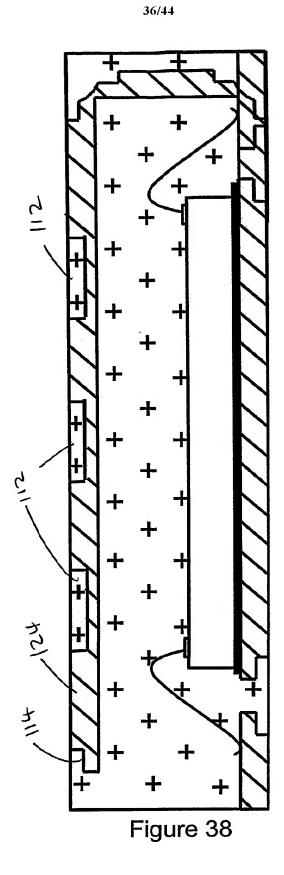
Figure 33

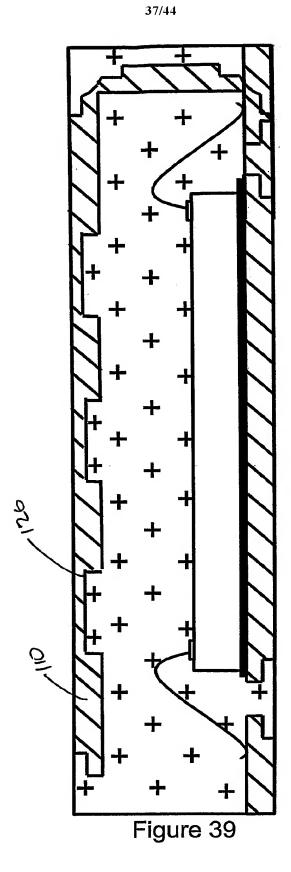


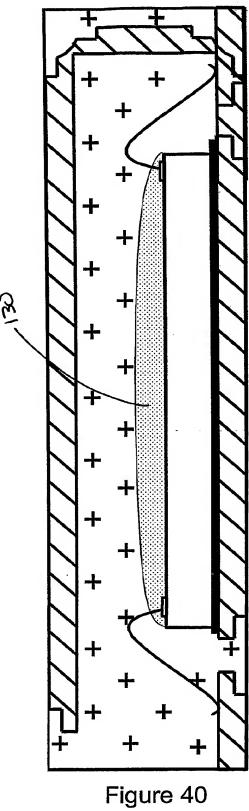


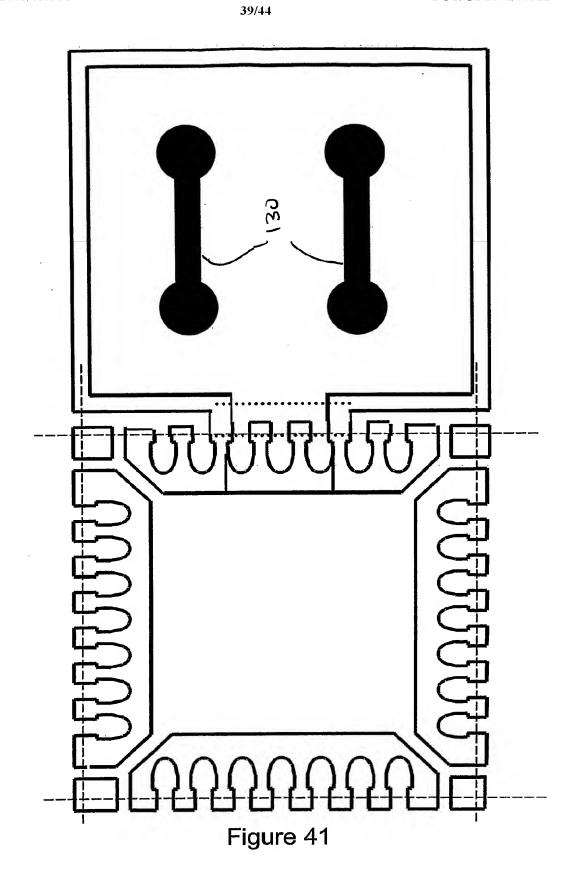


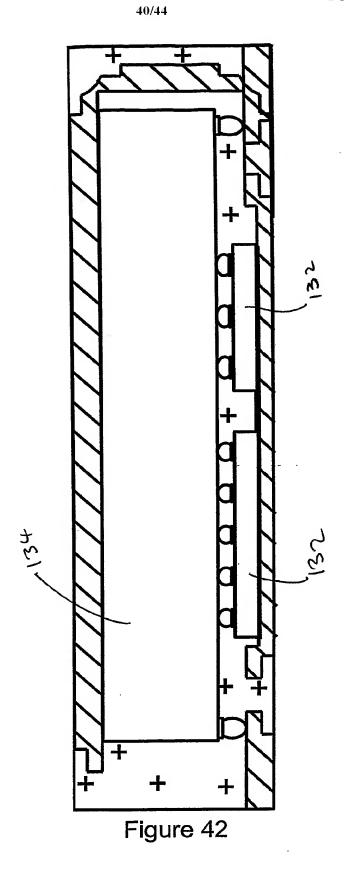


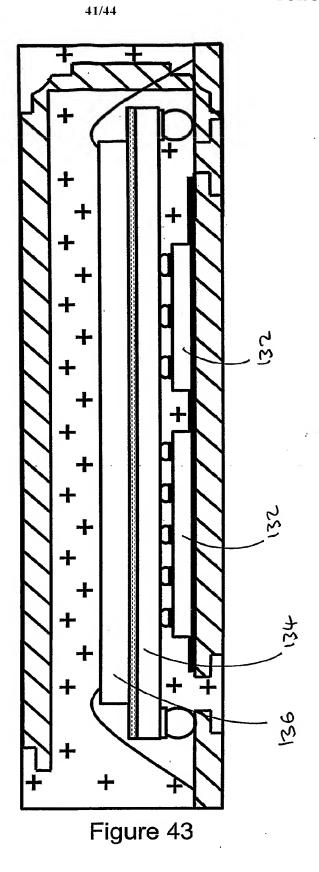


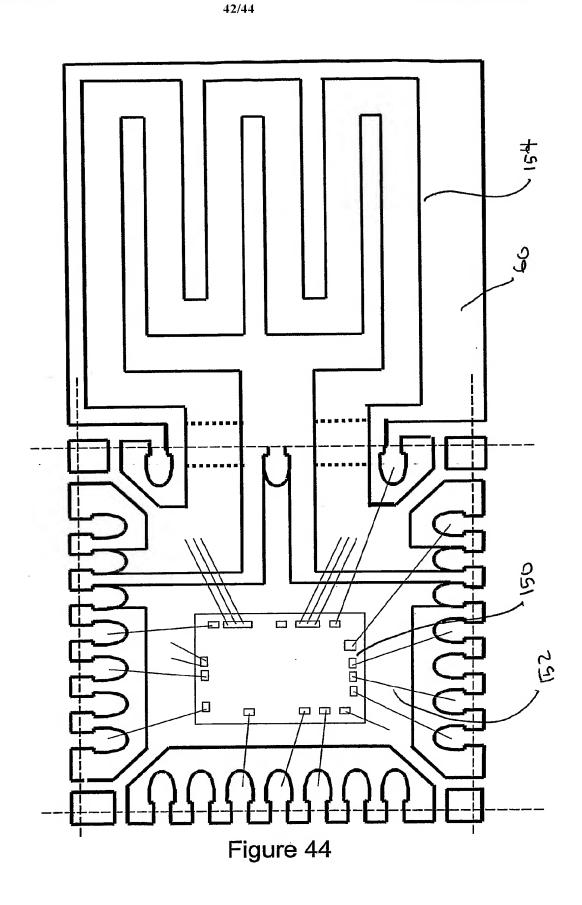


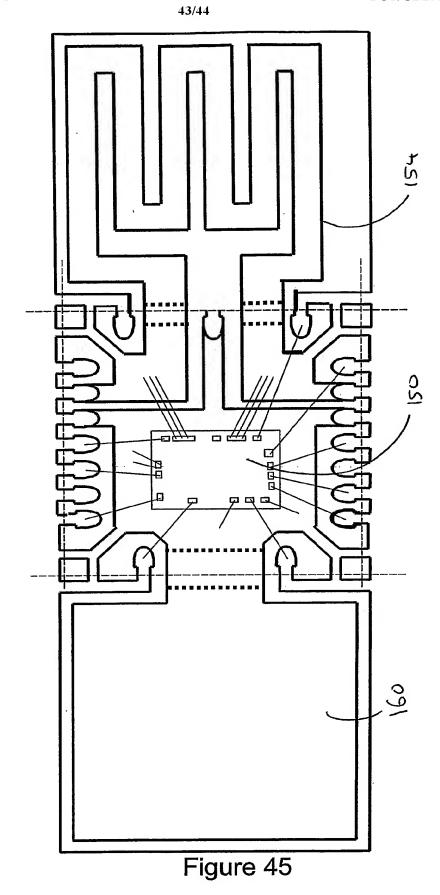












Monitor Point	Frequenc	Std Pkg		New Pkg.		Shield Effectiveness	
		E	Н	E	Н	E Field	H Field
	GHz	dBV/m	dBA/m	dBV/m	dBA/m	dB	dB
+Z	0.9	-2	-21	-12	-42	10	21
+Z	2.4	7	-22	-4	-42	11	20
+Z	5.2	13	-22	5	-41	8	19
+Z	10.0	16	-19	11	-39	5	20

Fig. 46

Semiconductor Chip	Die Size	Material	Power Dissipation
Daughter Die 1	1.8x0.9x0.2mm	Silicon	100mW
Daughter Die 2	2.1x1.1x0.2mm	Gallium Arsenide	1W
Mother Die 3	2.65x2.65x0.2mm	Glass-Quartz	100mW

Fig. 47

Monitor Point	Standard Package	New Package	
	Temp (deg C)	Temp (deg C)	
Daughter Die 2	137	116	
% Improvement	-	22	

Fig. 48